











CSD25481F4

SLPS420D - SEPTEMBER 2013-REVISED OCTOBER 2014

# CSD25481F4 20 V P-Channel FemtoFET™ MOSFET

#### **Features**

- Ultra-Low On Resistance
- Ultra-Low Q<sub>a</sub> and Q<sub>ad</sub>
- High Operating Drain Current
- Ultra-Small Footprint (0402 Case Size)
  - 1 mm  $\times$  0.6 mm
- Ultra-Low Profile
  - 0.35 mm Max Height
- Integrated ESD Protection Diode
  - Rated >4 kV HBM
  - Rated >2 kV CDM
- Lead and Halogen Free
- **RoHS Compliant**

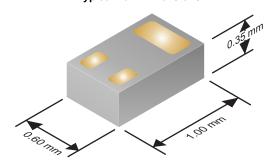
## 2 Applications

- Optimized for Load Switch Applications
- Optimized for General Purpose Switching **Applications**
- **Battery Applications**
- Handheld and Mobile Applications

#### 3 Description

This 90 mΩ, 20 V P-Channel FemtoFET™ MOSFET is designed and optimized to minimize the footprint in many handheld and mobile applications. This technology is capable of replacing standard small signal MOSFETs while providing at least a 60% reduction in footprint size.

**Typical Part Dimensions** 



#### **Product Summary**

T <sub>A</sub> = 25°	С	TYPICAL VA	UNIT	
$V_{DS}$	Drain-to-Source Voltage		V	
$Q_g$	Gate Charge Total (-4.5 V)	913		рС
$Q_{gd}$	Gate Charge Gate-to-Drain	153		рС
		$V_{GS} = -1.8 \text{ V}$	395	mΩ
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = -2.5 V	145	mΩ
	- Chi riddidianid	V <sub>GS</sub> = -4.5 V 90		mΩ
V <sub>GS(th)</sub>	Threshold Voltage	-0.95		٧

## Ordering Information<sup>(1)</sup>

Device	Qty	Media	Package	Ship
CSD25481F4	3000	7-Inch Reel	Femto(0402)	Tape and
CSD25481F4T	250	7-Inch Reel	Land Grid Array (LGA)	Reel

(1) For all available packages, see the orderable addendum at the end of the data sheet.

#### **Absolute Maximum Ratings**

T <sub>4</sub> = 25	T <sub>A</sub> = 25°C unless otherwise stated VALUE							
V <sub>DS</sub>	Drain-to-Source Voltage	-20	UNIT V					
V <sub>GS</sub>	Gate-to-Source Voltage -12							
I <sub>D</sub>	Continuous Drain Current <sup>(1)</sup> –2.5							
I <sub>DM</sub>	Pulsed Drain Current <sup>(2)</sup>	-10	Α					
	Continuous Gate Clamp Current	-35	mA					
l <sub>G</sub>	Pulsed Gate Clamp Current <sup>(2)</sup>	-350	mA					
$P_D$	Power Dissipation <sup>(1)</sup>	500	mW					
V	Human Body Model (HBM)	4	kV					
V <sub>(ESD)</sub>	Charged Device Model (CDM)	2	kV					
T <sub>J</sub> , T <sub>stg</sub>	Operating Junction and Storage Temperature Range	-55 to 150	°C					

- (1) Typical  $R_{\theta JA} = 85^{\circ} \text{C/W}$  on 1 inch<sup>2</sup> (6.45 cm<sup>2</sup>), 2 oz. (0.071 mm thick) Cu pad on a 0.06 inch (1.52 mm) thick FR4 PCB.
- (2) Pulse duration ≤ 300 µs, duty cycle ≤ 2%

**Top View** 

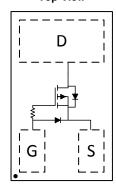




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## **4 Revision History**

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

Changes from Revision C (February 2014) to Revision D						
Corrected timing V <sub>DS</sub> to read –10 V						
Changes from Revision B (February 2013) to Revision C	Page					
Corrected capacitance units to read pF in Figure 5	5					
Changes from Revision A (December 2013) to Revision B	Page					
Updated lead and halogen free in features						
Added I <sub>G</sub> parameter						
Lowered I <sub>DSS</sub> limit	3					
Lowered I <sub>GSS</sub> limit	3					
Changes from Original (September 2013) to Revision A	Page					
Took out jumbo reel info and added small reel info	1					
Removed UIS graph	5					
Corrected device name	10					

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# 5 Specifications

#### 5.1 Electrical Characteristics

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS					
BV <sub>DSS</sub>	Drain-to-Source Voltage	$V_{GS} = 0 \text{ V}, I_{DS} = -250 \mu\text{A}$	-20			V
I <sub>DSS</sub>	Drain-to-Source Leakage Current	V <sub>GS</sub> = 0 V, V <sub>DS</sub> = -16 V			-100	nA
I <sub>GSS</sub>	Gate-to-Source Leakage Current	V <sub>DS</sub> = 0 V, V <sub>GS</sub> = -12 V			-50	nA
V <sub>GS(th)</sub>	Gate-to-Source Threshold Voltage	$V_{DS} = V_{GS}, I_{DS} = -250 \mu A$	-0.7	-0.95	-1.2	V
		$V_{GS} = -1.8 \text{ V}, I_{DS} = -0.1 \text{ A}$		395	800	mΩ
Ь	Drain to Course On Registeres	$V_{GS} = -2.5 \text{ V}, I_{DS} = -0.5 \text{ A}$		145	174	mΩ
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	$V_{GS} = -4.5 \text{ V}, I_{DS} = -0.5 \text{ A}$		90	105	mΩ
		$V_{GS} = -8 \text{ V}, I_{DS} = -0.5 \text{ A}$		75	88	mΩ
9 <sub>fs</sub>	Transconductance	$V_{DS} = -10 \text{ V}, I_{DS} = -0.5 \text{ A}$		3.3		S
DYNAMI	IC CHARACTERISTICS					
C <sub>iss</sub>	Input Capacitance	189		189		pF
C <sub>oss</sub>	Output Capacitance	$V_{GS} = 0 \text{ V}, V_{DS} = -10 \text{ V},$ f = 1  MHz		78		pF
C <sub>rss</sub>	Reverse Transfer Capacitance	) - 1 Will2		5.5		pF
R <sub>G</sub>	Series Gate Resistance			20		Ω
Qg	Gate Charge Total (4.5 V)			913		рС
$Q_{gd}$	Gate Charge Gate-to-Drain	V 40 V I 05 A		153		рС
Q <sub>gs</sub>	Gate Charge Gate-to-Source	$V_{DS} = -10 \text{ V}, I_{DS} = -0.5 \text{ A}$		240		рС
Q <sub>g(th)</sub>	Gate Charge at V <sub>th</sub>			116		рС
Q <sub>oss</sub>	Output Charge	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V		1030		рС
t <sub>d(on)</sub>	Turn On Delay Time			4.1		ns
t <sub>r</sub>	Rise Time	$V_{DS} = -10 \text{ V}, V_{GS} = -4.5 \text{ V},$		3.6		ns
t <sub>d(off)</sub>	Turn Off Delay Time	$I_{DS} = -0.5 \text{ A}, R_G = 2 \Omega$		16.9		ns
$t_f$	Fall Time		6.7		ns	
DIODE C	CHARACTERISTICS					
V <sub>SD</sub>	Diode Forward Voltage	$I_{SD} = -0.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.75		V
Q <sub>rr</sub>	Reverse Recovery Charge	V 40.V I 0.5 A 4/4 400.A/	1010			рС
t <sub>rr</sub>	Reverse Recovery Time	$V_{DS} = -10 \text{ V}, I_F = -0.5 \text{ A}, di/dt = 100 \text{ A/}\mu\text{s}$				ns

#### 5.2 Thermal Information

(T<sub>A</sub> = 25°C unless otherwise stated)

	THERMAL METRIC	TYPICAL VALUES	UNIT
D	Junction-to-Ambient Thermal Resistance (1)	85	°C/W
$R_{\theta JA}$	Junction-to-Ambient Thermal Resistance (2)	245	· C/vv

<sup>(1)</sup> Device mounted on FR4 material with 1 inch² (6.45 cm²), 2 oz. (0.071 mm thick) Cu.

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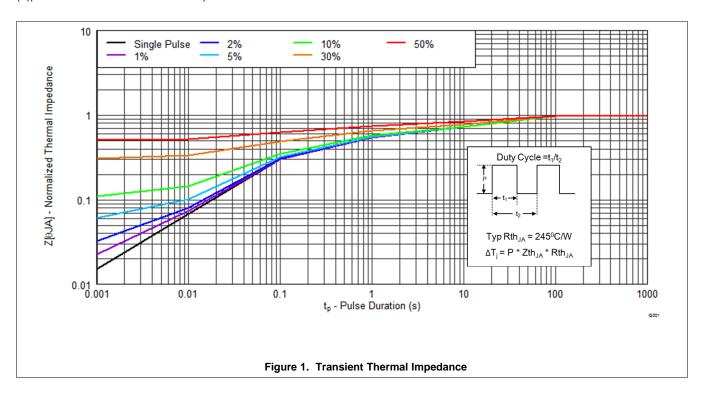
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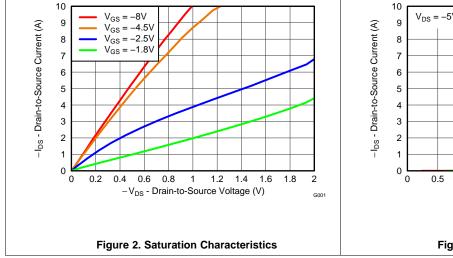
<sup>(2)</sup> Device mounted on FR4 material with minimum Cu mounting area.

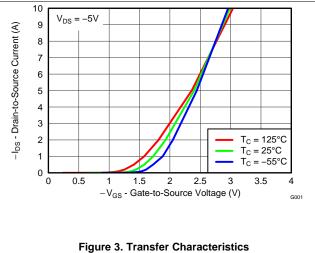


## 5.3 Typical MOSFET Characteristics

(T<sub>A</sub> = 25°C unless otherwise stated)







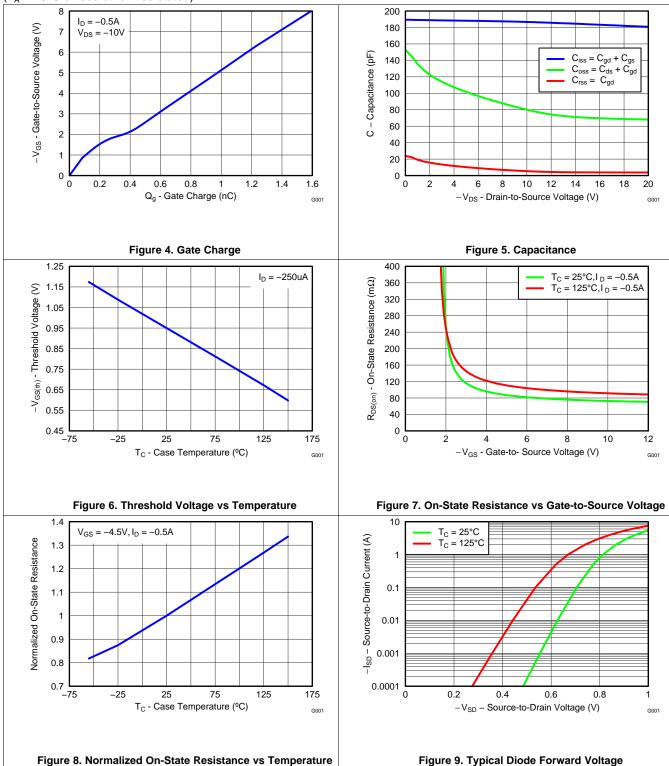
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#### **Typical MOSFET Characteristics (continued)**

(T<sub>A</sub> = 25°C unless otherwise stated)



175



50

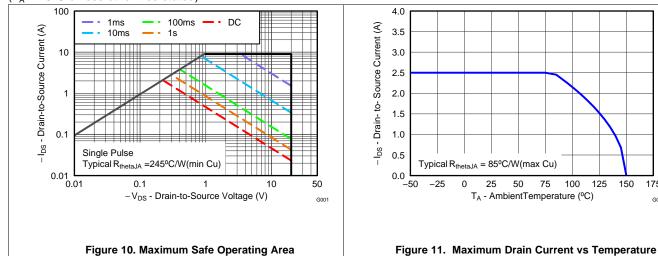
75

100

125

## **Typical MOSFET Characteristics (continued)**

 $(T_A = 25^{\circ}C \text{ unless otherwise stated})$ 





# 6 Device and Documentation Support

#### 6.1 Trademarks

FemtoFET is a trademark of Texas Instruments.
All other trademarks are the property of their respective owners.

#### 6.2 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

## 6.3 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

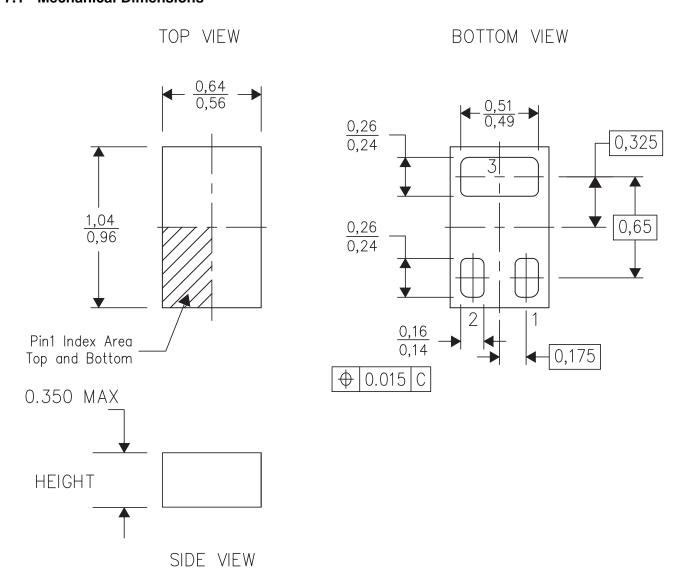
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#### 7 Mechanical Data

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

#### 7.1 Mechanical Dimensions



- (1) All linear dimensions are in millimeters (dimensions and tolerancing per AME T14.5M-1994).
- (2) This drawing is subject to change without notice.
- (3) This package is a PB-free solder land design.

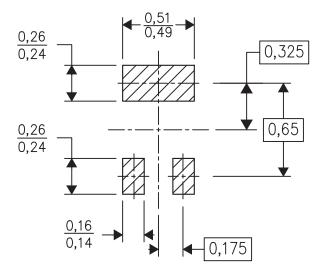
**Pin Configuration** 

Position	Designation
Pin 1	Gate
Pin 2	Source
Pin 3	Drain

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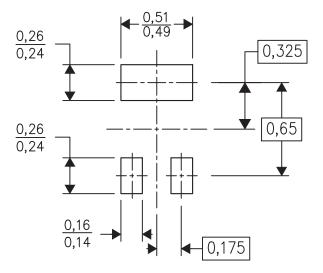


# 7.2 Recommended Minimum PCB Layout



(1) All dimensions are in millimeters.

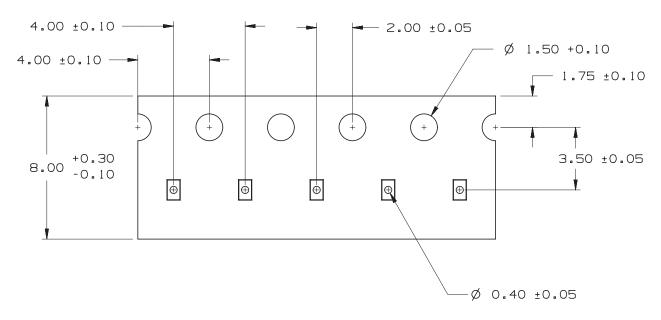
## 7.3 Recommended Stencil Pattern

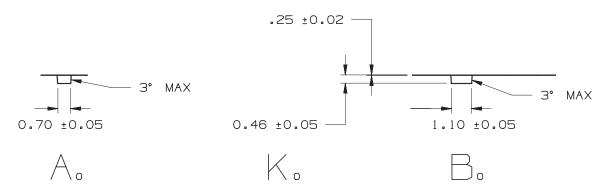


(1) All dimensions are in millimeters.



## 7.4 CSD25481F4 Embossed Carrier Tape Dimensions





(1) Pin 1 is oriented in the top-right quadrant of the tape enclosure (quadrant 2), closest to the carrier tape sprocket



## PACKAGE OPTION ADDENDUM

29-Oct-2014

#### PACKAGING INFORMATION

Orderable Device	Status	Package Type	Package Drawing	Pins	Package Qty		Lead/Ball Finish	MSL Peak Temp	Op Temp (°C)	Device Marking	Samples
	(1)		Diawing		αιy	(2)	(6)	(3)		(4/5)	
CSD25481F4	ACTIVE	PICOSTAR	YJC	3	3000	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	CS	Samples
CSD25481F4T	ACTIVE	PICOSTAR	YJC	3	250	Green (RoHS & no Sb/Br)	Call TI	Level-1-260C-UNLIM	-55 to 150	CS	Samples

(1) The marketing status values are defined as follows:

**ACTIVE:** Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.

**TBD:** The Pb-Free/Green conversion plan has not been defined.

**Pb-Free (RoHS):** TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

**Pb-Free (RoHS Exempt):** This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

- (3) MSL, Peak Temp. The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead/Ball Finish Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead/Ball Finish values may wrap to two lines if the finish value exceeds the maximum column width.

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# **PACKAGE OPTION ADDENDUM**

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PACKAGE MATERIALS INFORMATION

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## TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	Package Type	Package Drawing			Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD25481F4	PICOST AR	YJC	3	3000	180.0	8.4	0.7	1.1	0.46	4.0	8.0	Q2

**PACKAGE MATERIALS INFORMATION** 

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#### \*All dimensions are nominal

Device Package Typ		Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)	
CSD25481F4	PICOSTAR	YJC	3	3000	182.0	182.0	17.0	

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